



SSCN3356GS6

NPN Switching Transistor

➤ Features

VCB	VCE	VEB	IC
20V	12V	3V	0.1A

➤ Description

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-23 package, which is designed for telephony and professional communication equipment.

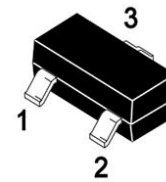
➤ Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

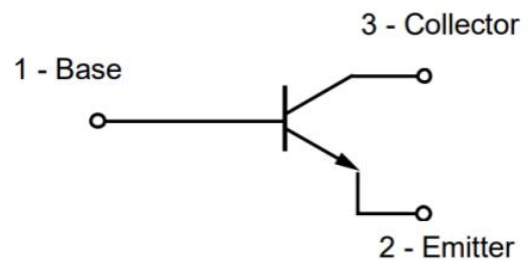
➤ Ordering Information

Device	Package	Shipping
SSCN3356GS6	SOT-23	3000/Reel

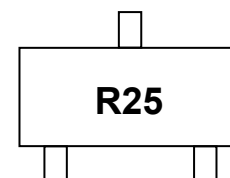
➤ Pin configuration



SOT-23



Circuit Diagram



Marking(Top View)



➤ **Absolute Maximum Ratings**($T_A = 25^\circ\text{C}$ unless otherwise noted)

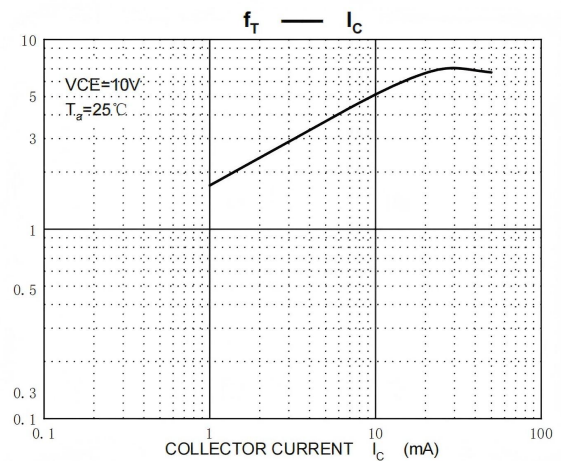
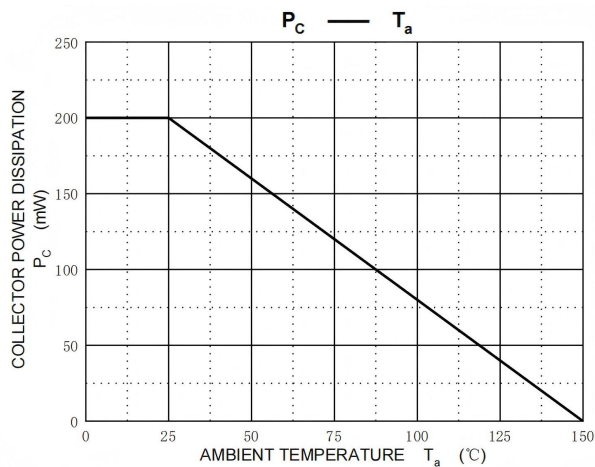
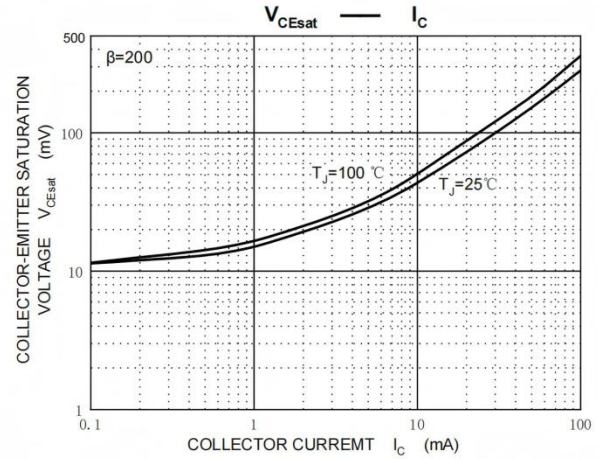
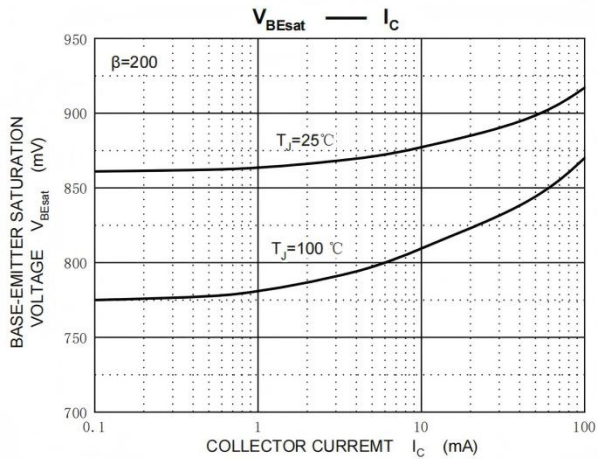
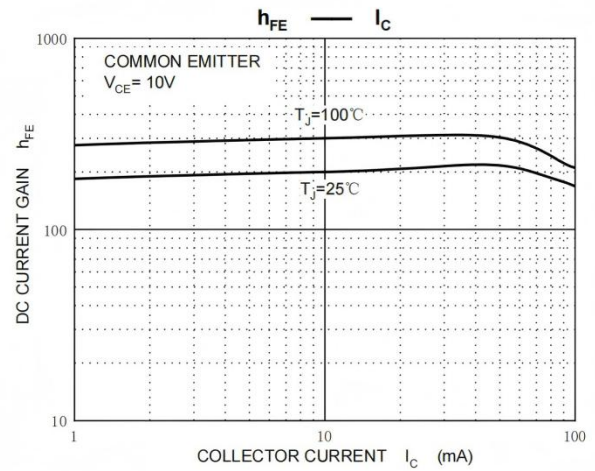
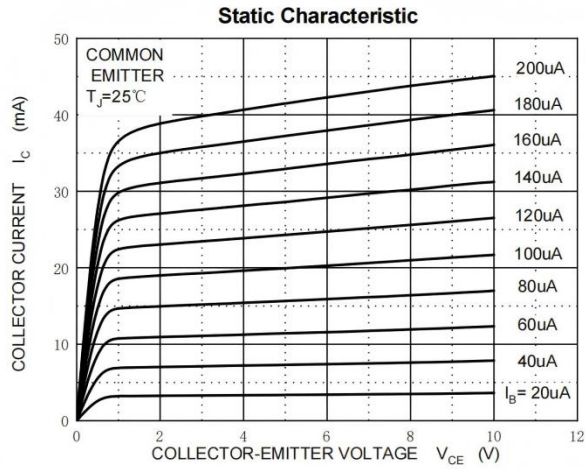
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	20	V
Collector- Emitter Voltage	V_{CE0}	12	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current-Continuous	I_C	0.1	A
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$

➤ **Electrical Characteristics** ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 100\mu\text{A}, I_E = 0$	20			V
Collector-emitter Breakdown Voltage	BV_{CE0}	$I_C = 1\text{mA}, I_B = 0$	12			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E = 100\mu\text{A}, I_C = 0$	3			V
Collector Cutoff Current	I_{CB0}	$V_{CB} = 10\text{V}, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 1\text{V}, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$	125		250	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.3	V
Base-Emitter Saturation Base-Emitter	$V_{BE(sat)}$	$I_B = 50\text{mA}, I_C = 5\text{mA}$			1.15	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 20\text{mA}$		7		GHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$ $f = 1\text{MHz}$		0.8	1	pF

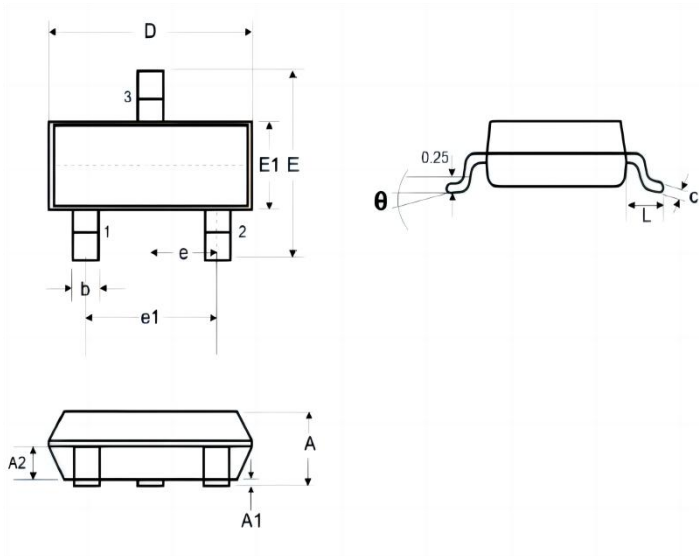


➤ Typical Performance Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)



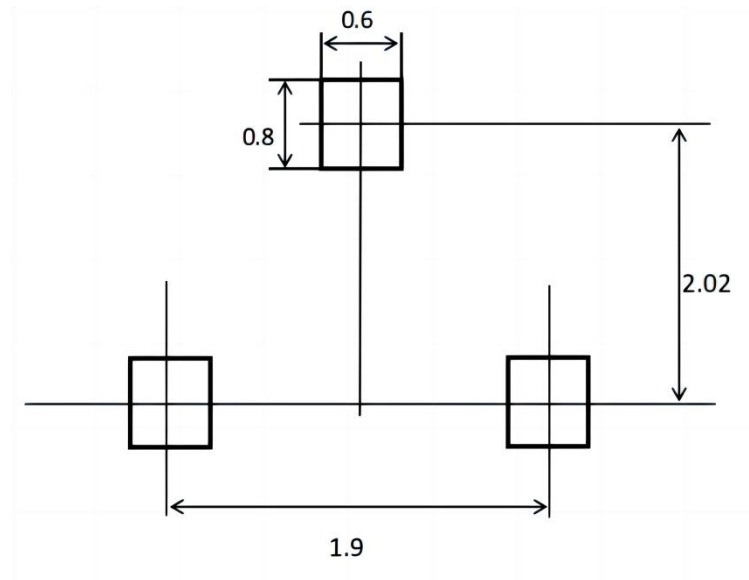
➤ Package Information

SOT-23



DIM	Millimeters		
	Min.	Typ.	Max.
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.51
c	0.08	-	0.18
D	2.800	2.90	3.000
E	2.10	2.37	2.64
E1	1.20	1.30	1.40
e	0.95		
e1	1.80	-	2.00
L	0.40	0.50	0.60
L1	0.30	-	0.50
θ	0°	-	8°

Recommended Pad outline (Unit: mm)





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